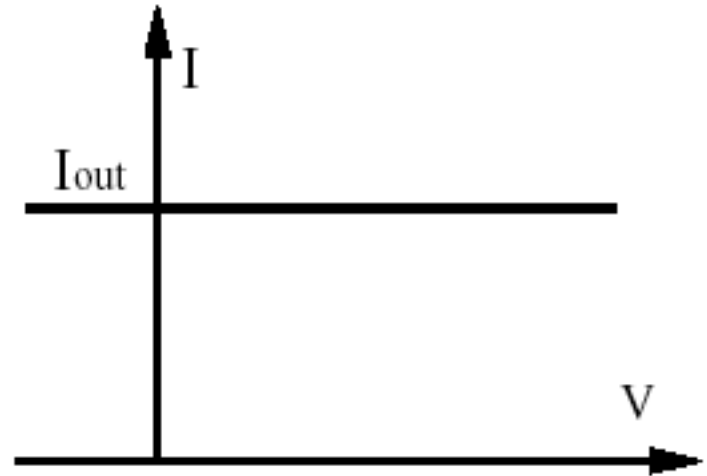
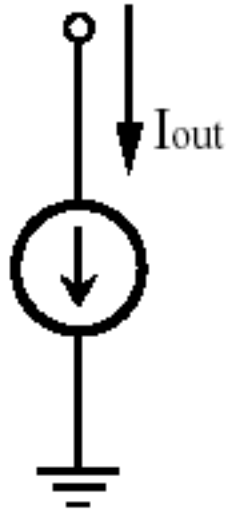


Lab 5 Review Slides

- **Current Source**
- **Active Load**
- **Bandwidth of Common Source Amplifier**

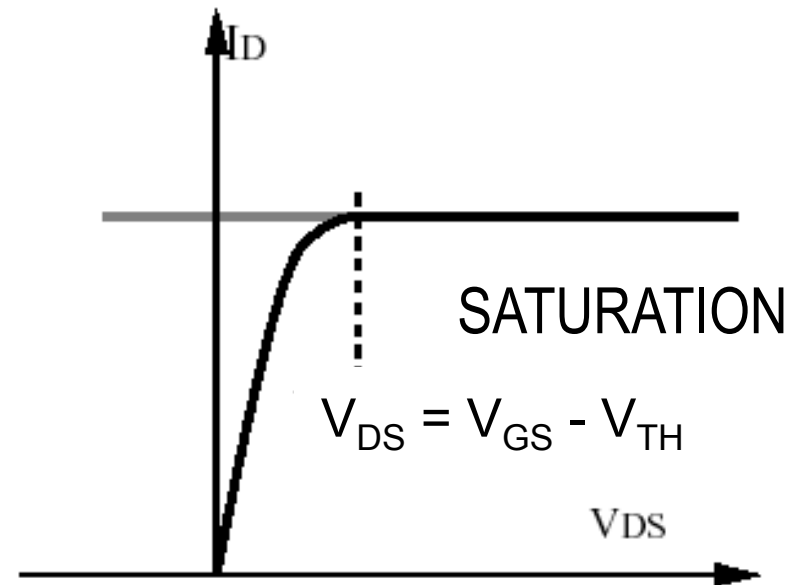
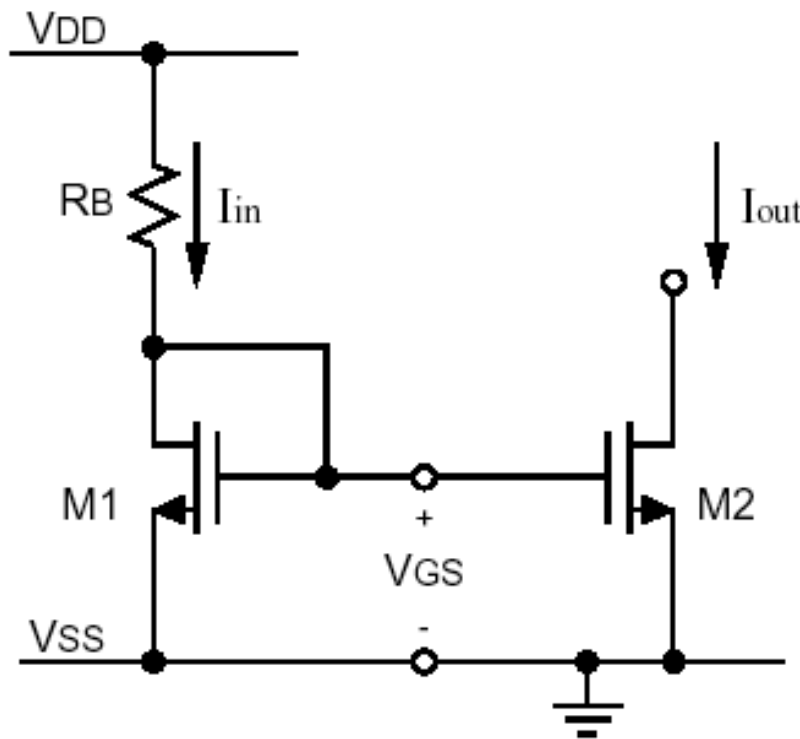
Current source

- Ideal goal
- Small signal model:
Open circuit
“ $R_D = \infty$ ”



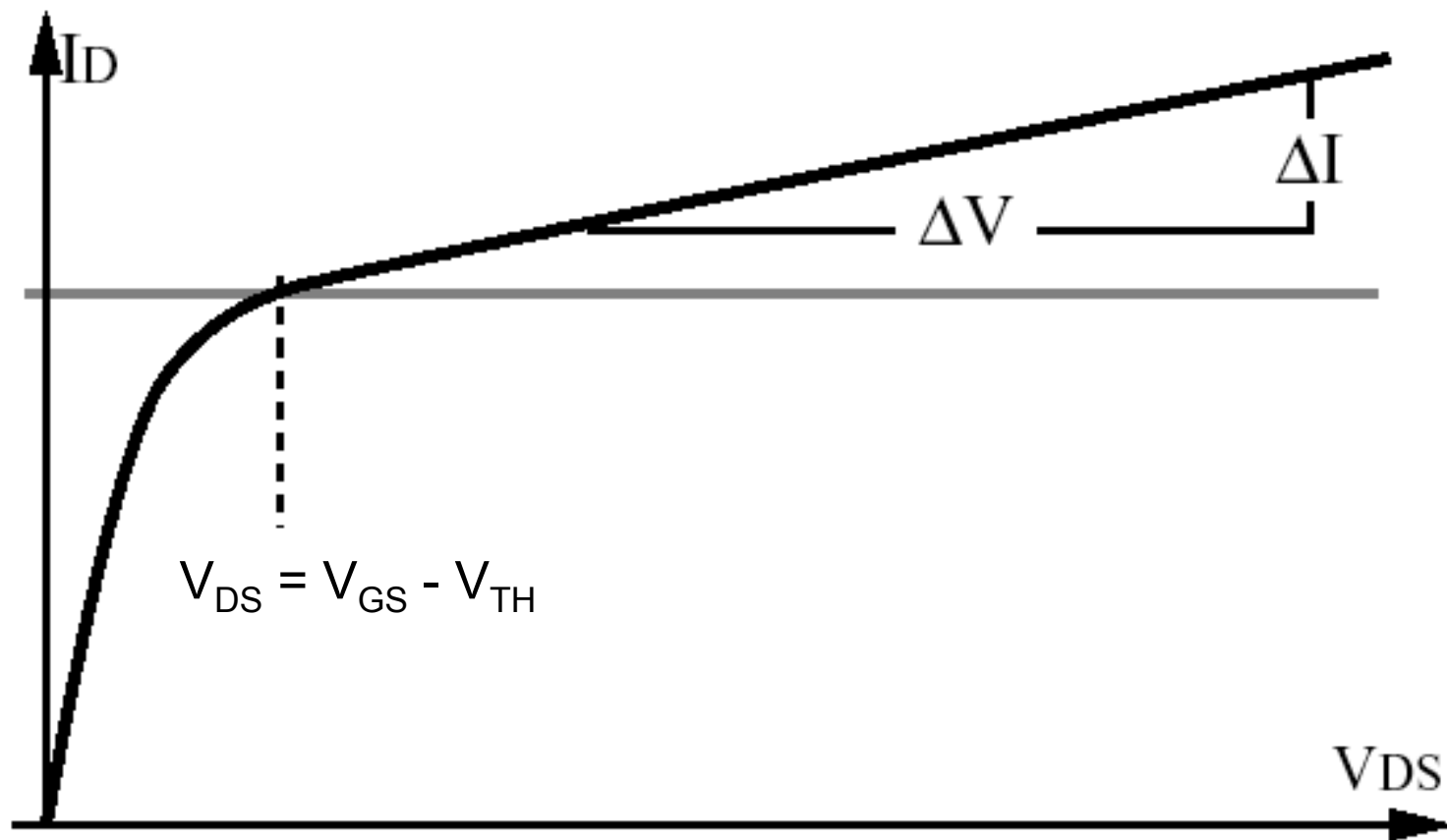
Realizing current source: MOSFET

- Large signal nonideality: "Compliance range"
- Looks like current source only for $V_{DS} > V_{GS} - V_{TH}$



MOSFET I_D - V_{DS} characteristic for fixed V_{GS}

- Small-signal nonideality: slope in active region

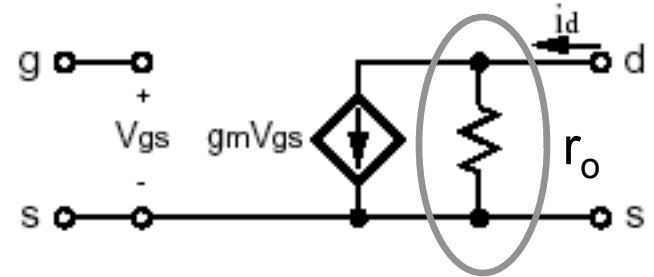
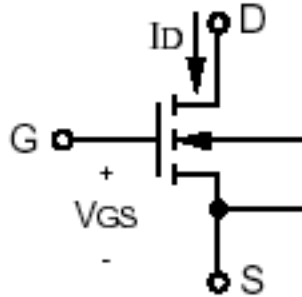


Modify small-signal model: Finite r_{ds} current source

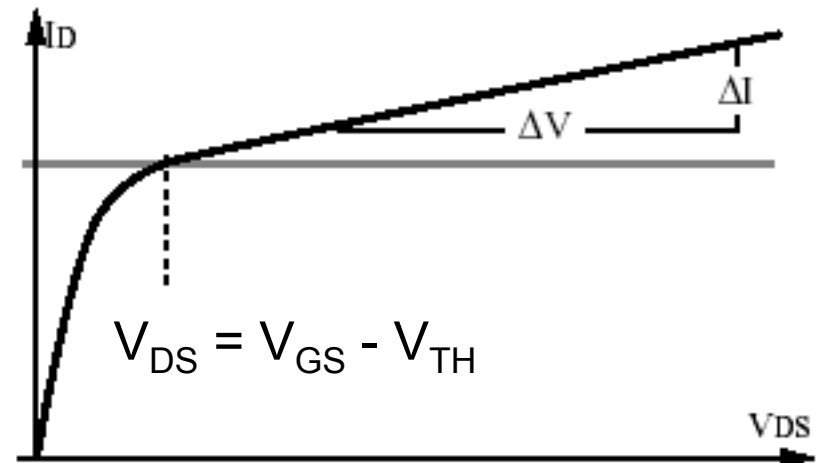
- Slope = $\Delta I / \Delta V$

$$r_o = \frac{\Delta V}{\Delta I}$$

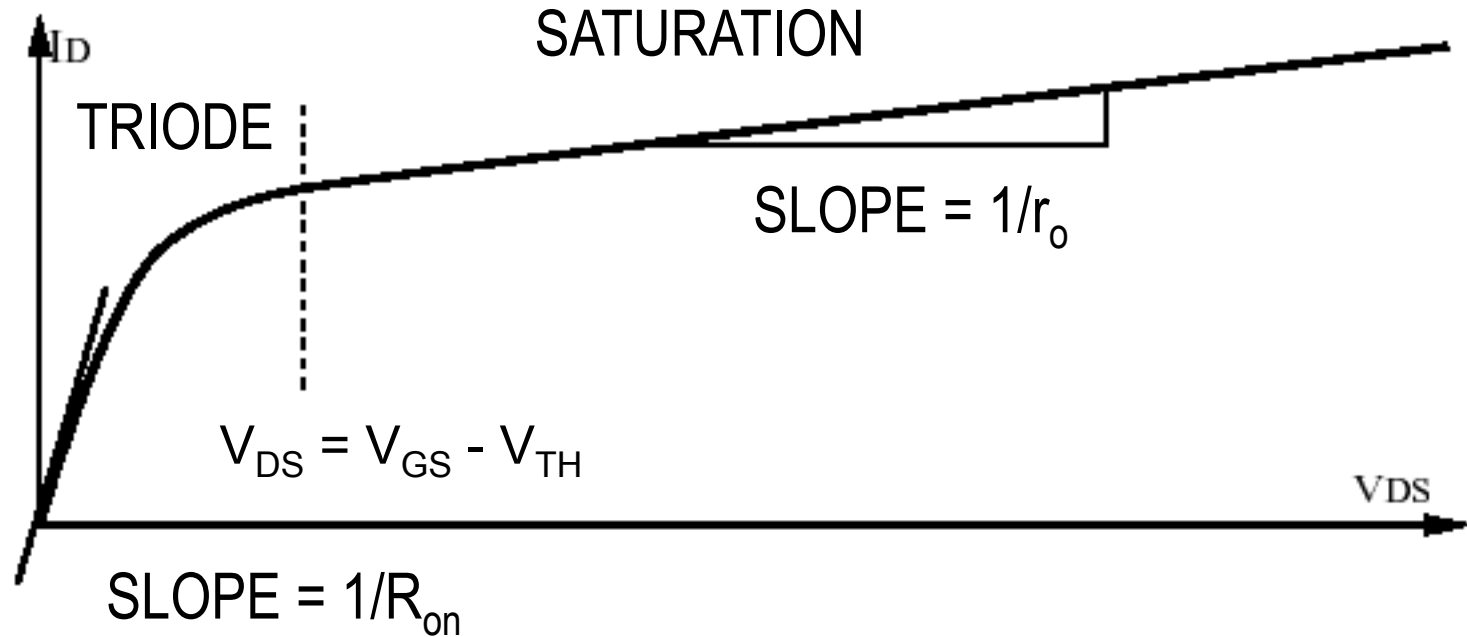
$$SLOPE = \frac{\Delta I}{\Delta V} = \frac{1}{r_o}$$



- Ideal:
zero slope
 $\Rightarrow r_o = \infty$



Caution: R_{on} vs. r_o confusion!



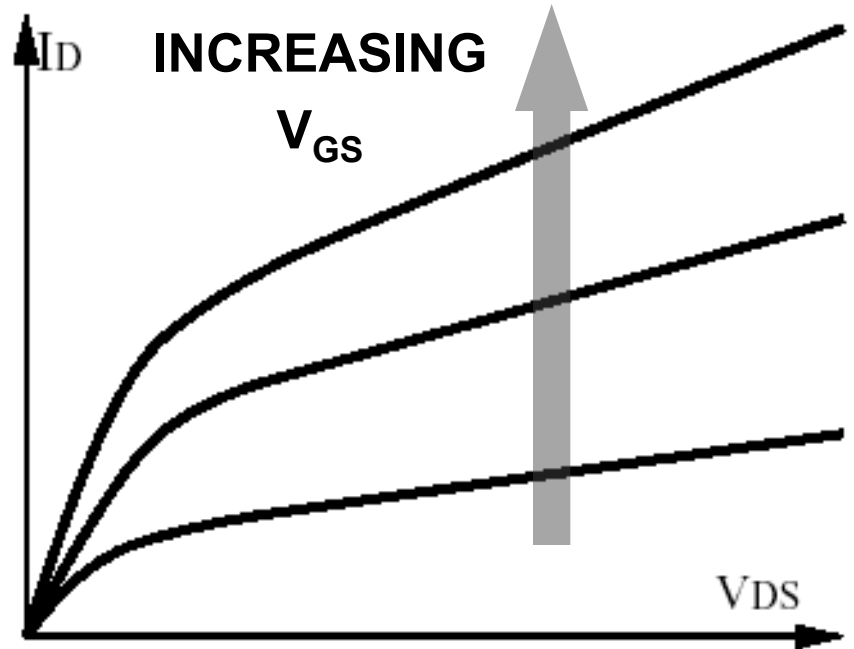
R_{on}

- Triode region
- Large signal
- True resistance
(V-I through origin)

r_o

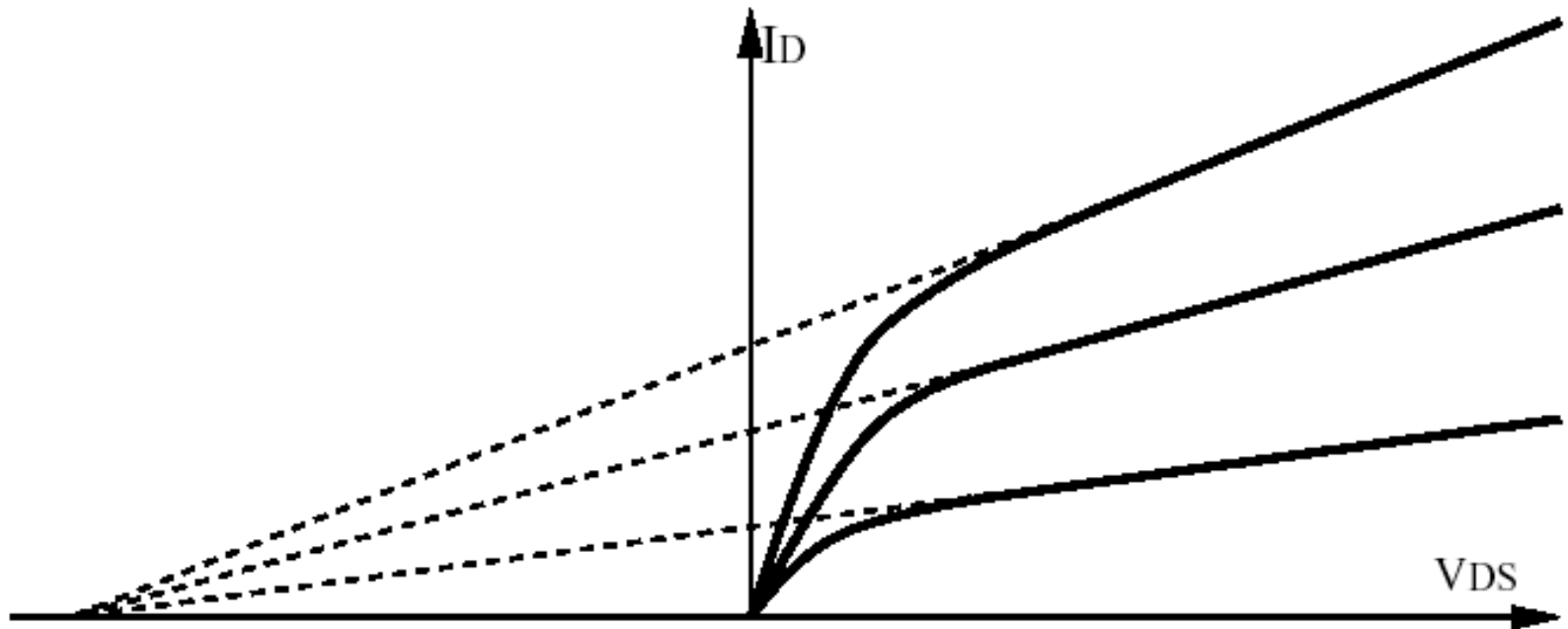
- Saturation region
- Small signal
- Models nonideality
of current source

I_D - V_{DS} Characteristic for Different V_{GS}



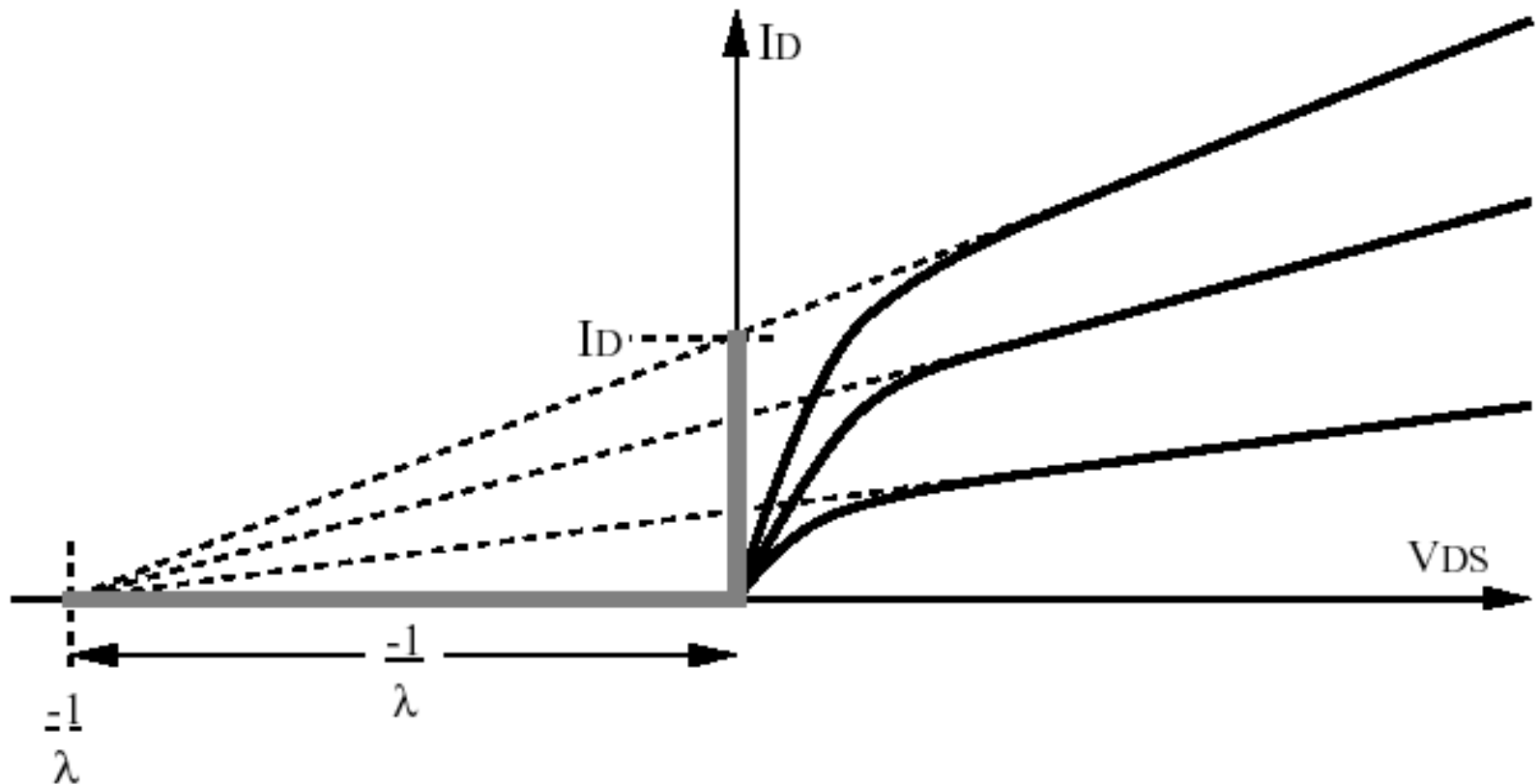
"Family" of curves

I_D - V_{DS} Characteristic for Different V_{GS}



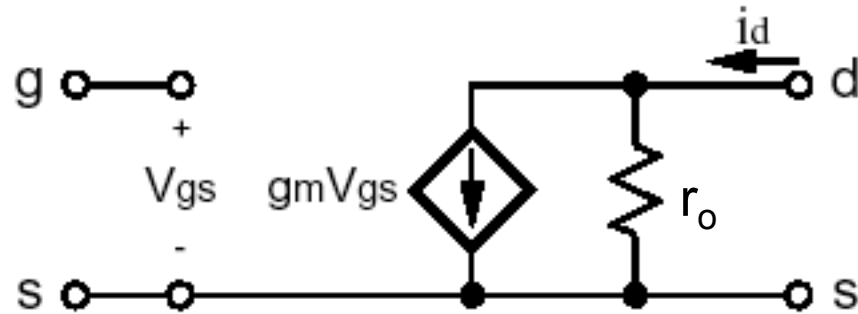
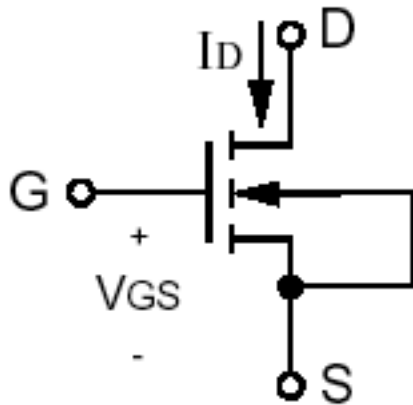
Extrapolate backward: intersect at V_{DS} -axis

1/slope provides small signal resistance r_o



- **Intersect at $-1/\lambda$** **Slope:** $\frac{1}{r_o} = \frac{I_D}{1/\lambda} \Rightarrow r_o = \frac{1}{\lambda I_D}$
- **Typical λ values:** **0.01 V^{-1} $L > 1\mu\text{m}$**
 0.2 V^{-1} $L < 1\mu\text{m}$

MOSFET small signal model



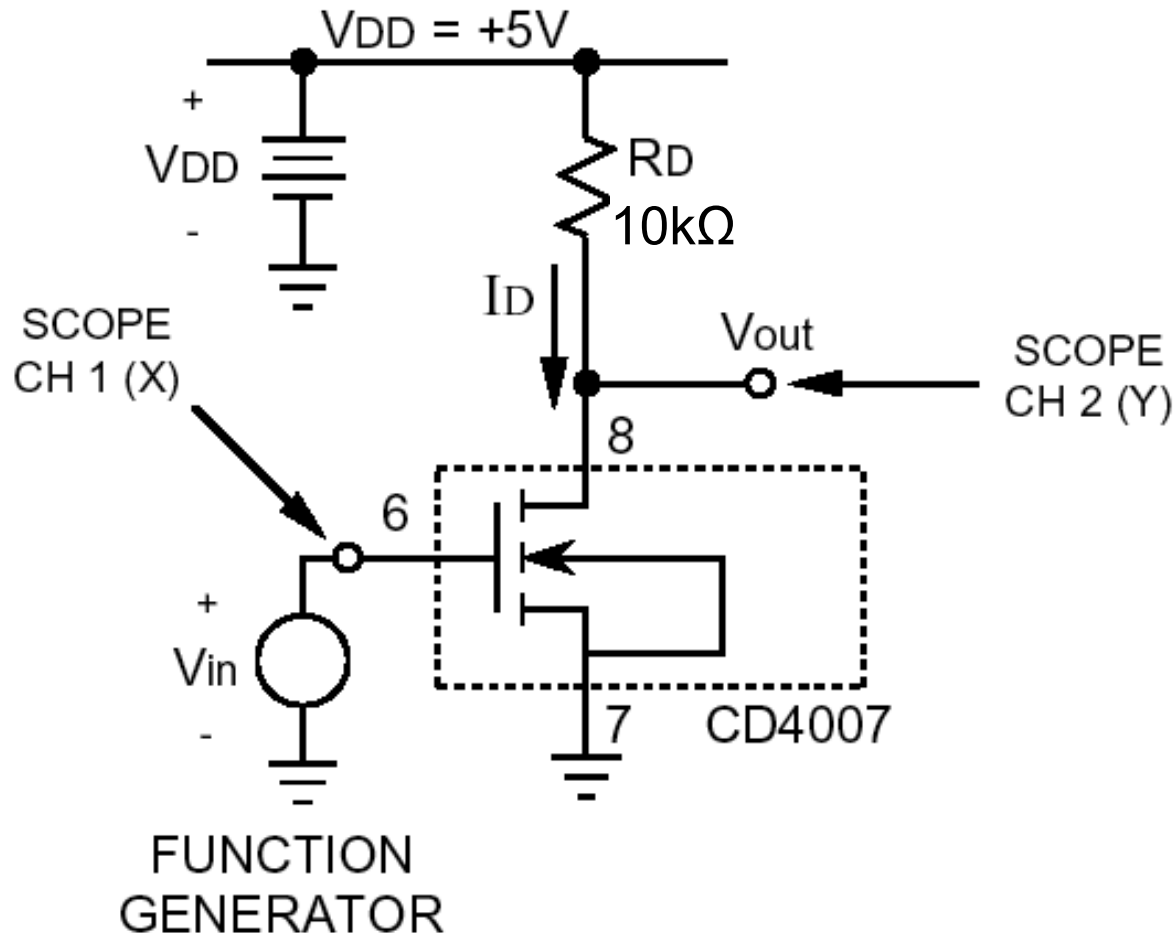
$$g_m = \frac{2I_D}{V_{GS} - V_{TH}} \quad r_o = \frac{1}{\lambda I_D}$$

- r_o in parallel: Model nonideality of current source due to channel length modulation

Increasing Gain

- **Typical gain (resistive load)**
 - **Class example: $|A_v| \approx 11.1$**
 - **Lab 4 example: $|A_v| < 10$**
- **How to increase A_v ?**

Common source circuit (Lab 4)



Setting operating point:

Adjusted function generator offset for DC output at midpoint of signal swing

Common source circuit (Lab 4)

- **DC operating point**
- **Chosen for V_{OUT} halfway between rails**
- **$I_D = 250 \mu A$**
- **$V_{GS} - V_{TH} \approx 0.5V - 1.0V$ (depends on parameters)**

$$V_{OUT} = V_{DD} - I_D R_D$$

$$V_{OUT} = +2.5V$$

$$I_D = \frac{V_{DD} - V_{OUT}}{R_D}$$

$$= \frac{5V - 2.5V}{10k\Omega} = 250\mu A$$

Common source circuit (Lab 4)

- **Small signal gain magnitude ≈ 10**
$$g_m = \frac{2I_D}{V_{eff}} = \frac{2(250\mu A)}{0.5V}$$
$$g_m = 1.0mA/V$$
- **Not impressive!**
$$A_v = -g_m R_D = -(1.0mA/V)(10k\Omega)$$
$$A_v = -10$$

How to increase A_v ?

Look at gain expression: $A_v = |g_m R_D|$

Increase R_D

- New $R_D = 100k\Omega$ (10X old value)

- Problem:

DC operating point

- Violates condition for saturation region: triode!

- DC operating point stuck at negative rail

$$V_{OUT} = V_{DD} - I_D R_D$$

$$V_{OUT} = 5V - \underbrace{(250\mu A)(100k\Omega)}_{25V}$$

$$V_{OUT} = -20V ?$$

Look at problem symbolically

- Use $g_m = 2I_D / (V_{GS} - V_{TH})$

$$g_m = \frac{2I_D}{V_{GS} - V_{TH}}$$

- $I_D R_D = \text{DC drop on load}$

$$|A_v| = g_m R_D = \frac{2I_D R_D}{V_{GS} - V_{TH}}$$

- Optimal bias at output:
constrained to $V_{DD} / 2$

$$I_D R_D = \frac{V_{DD}}{2}$$

- I_D, R_D not involved!

$$|A_v| = \frac{V_{DD}}{V_{GS} - V_{TH}}$$

- Value of approximate symbolic approach
vs. “exact” numerical results from simulation

How to increase gain (resistive load)

- **Increase V_{DD}**
 - usually fixed by application, process
- **Decrease $V_{GS} - V_{TH}$**
 - does increase g_m
 - but area penalty
 - Subthreshold for $V_{GS} - V_{TH} < 200 \text{ mV}$

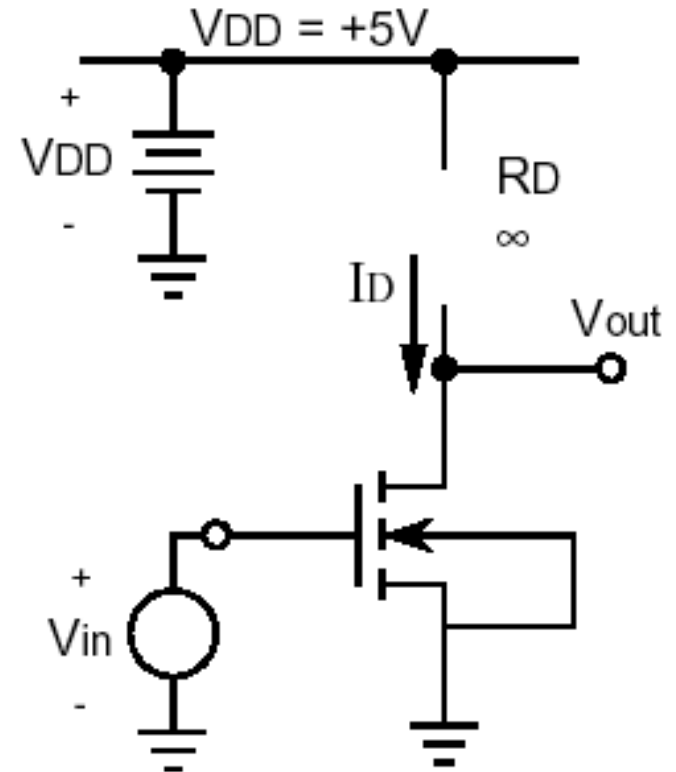
$$|A_v| = \frac{V_{DD}}{V_{GS} - V_{TH}}$$

Increase A_v : Different approach

- **Give up on resistive load ...**
- **What is highest resistance?**

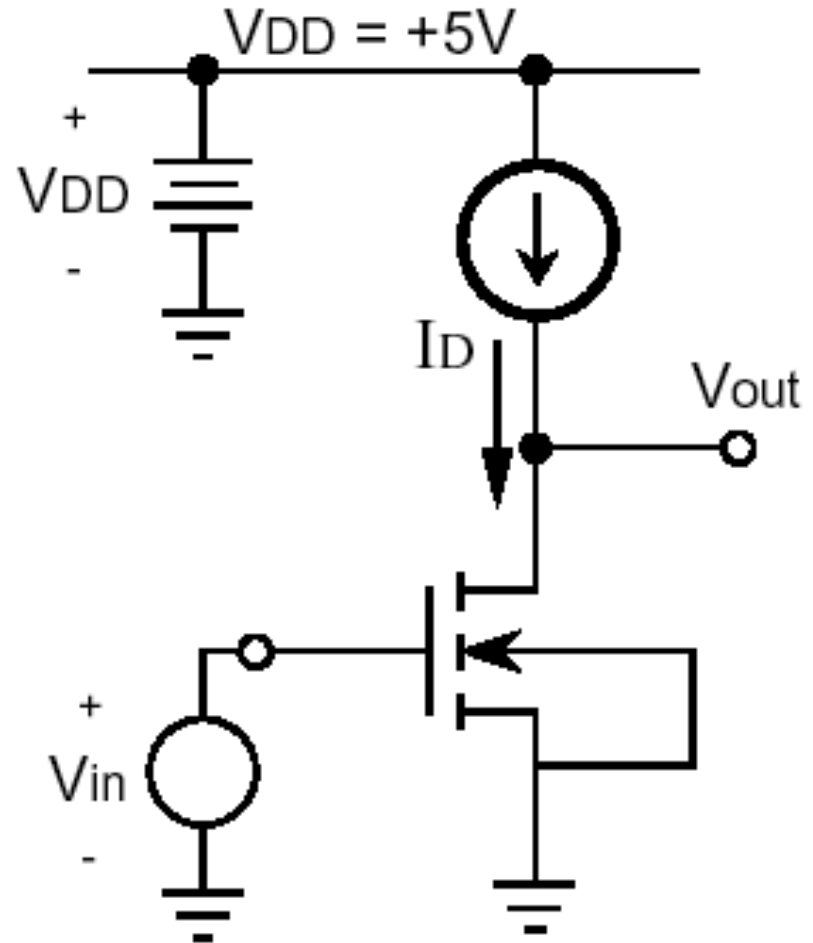
Increasing a_v : Different approach

- What is highest resistance?
- Infinite: open circuit
- Problem: no path for I_D
- Any circuit element that:
 - provides DC current, but
 - is open circuit in small signal model?



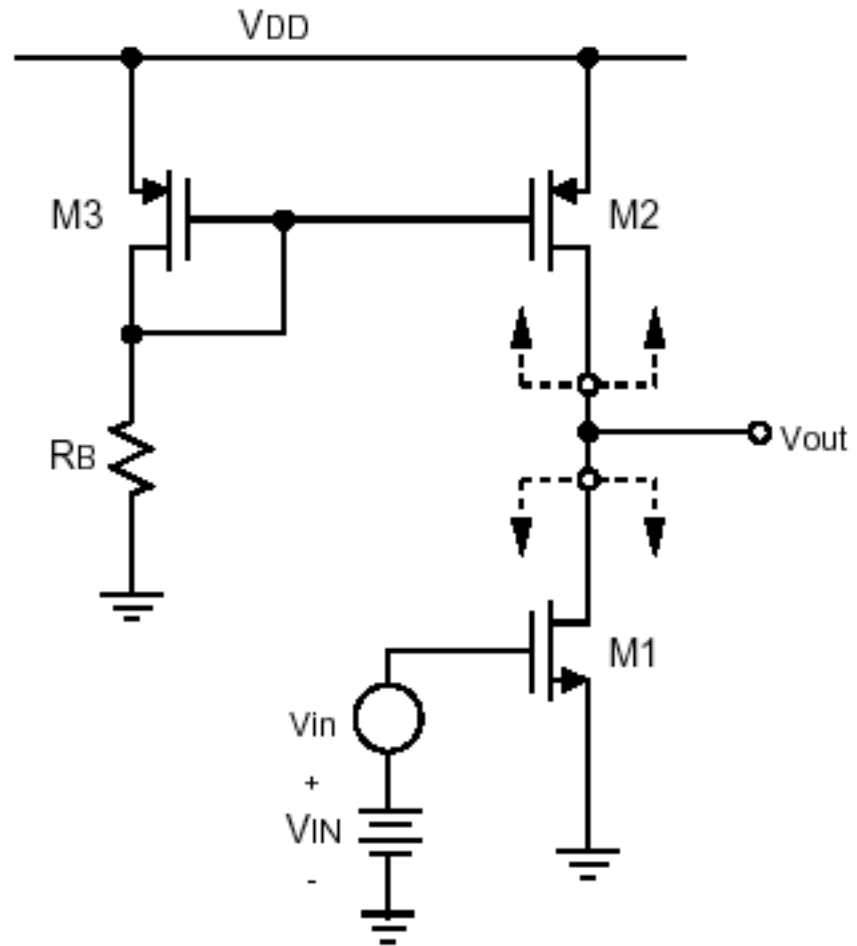
Current source!

- Open in small signal model
- Realizing current source: MOSFET



Lab Circuit: MOSFET with active load

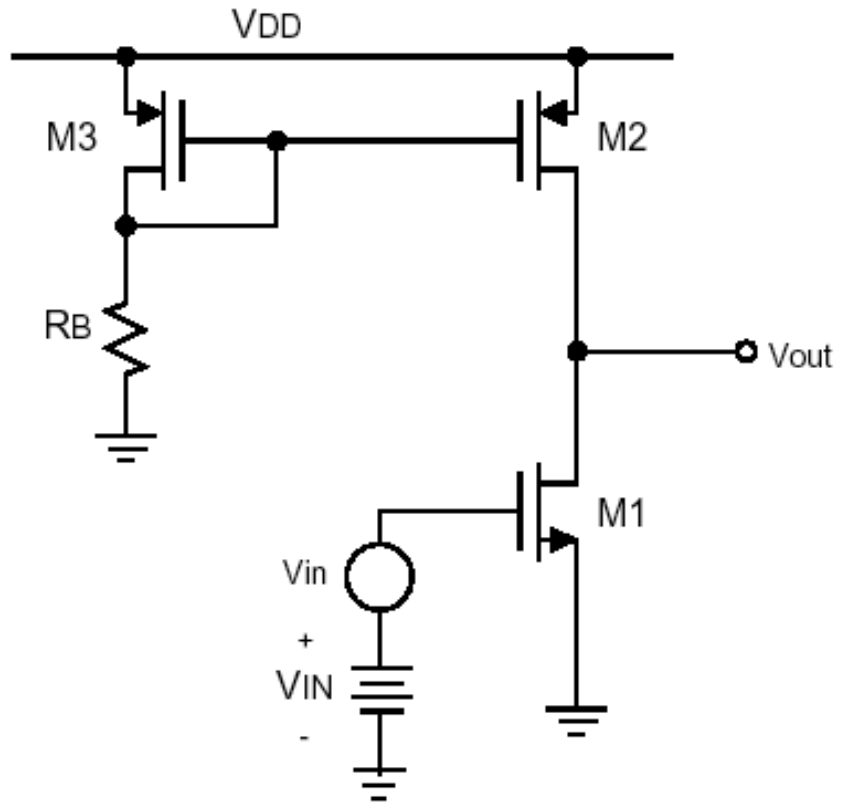
- Small signal model for M1
- Thevenin equivalent “looking into” drain of M2 (see J&M sec. 3.1)



Current source load: Large signal considerations

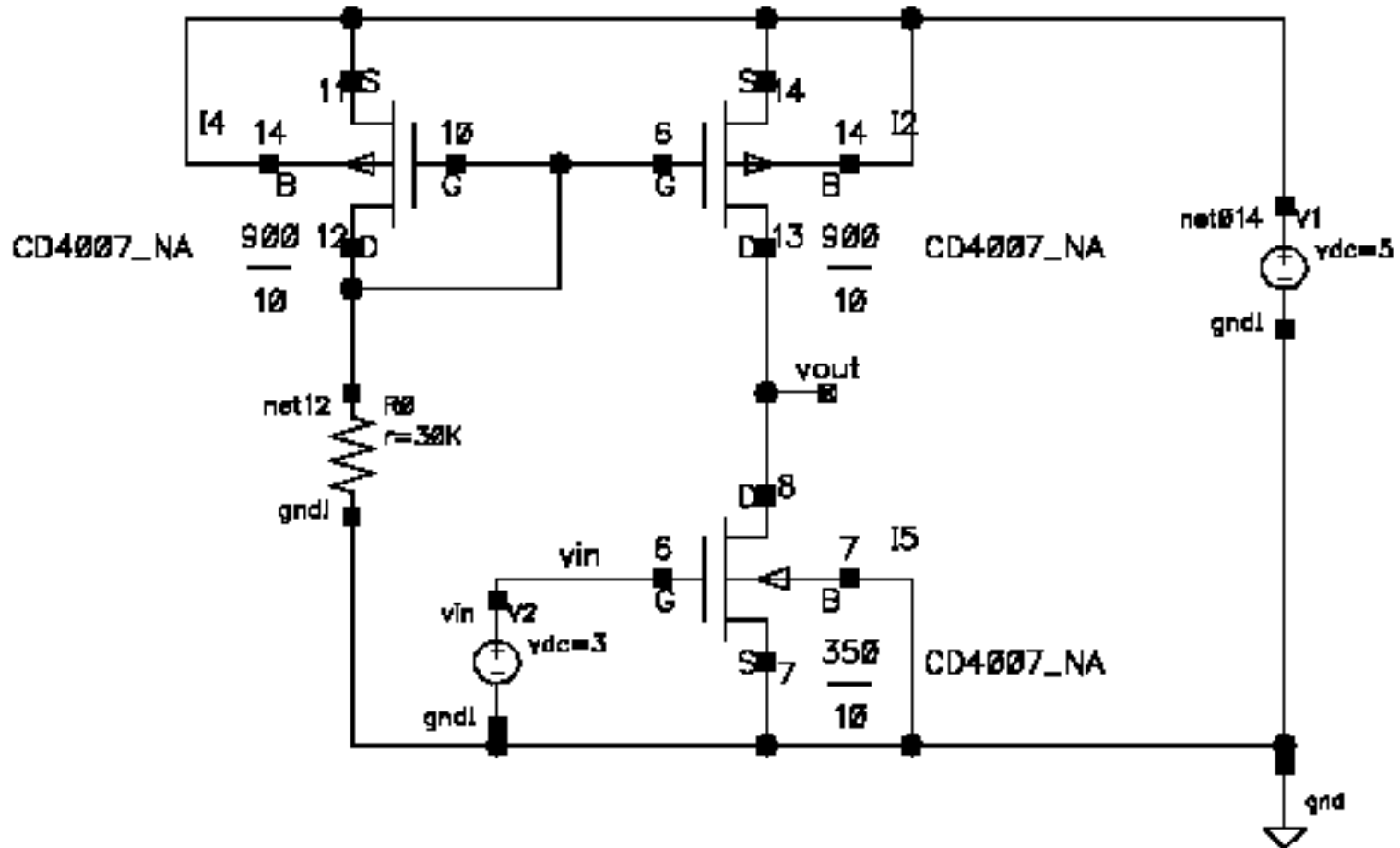
Output swing limits

- **Top:**
M2 “crash” into triode
- **Bottom:**
M1 crash into triode



Common Source with Active Load

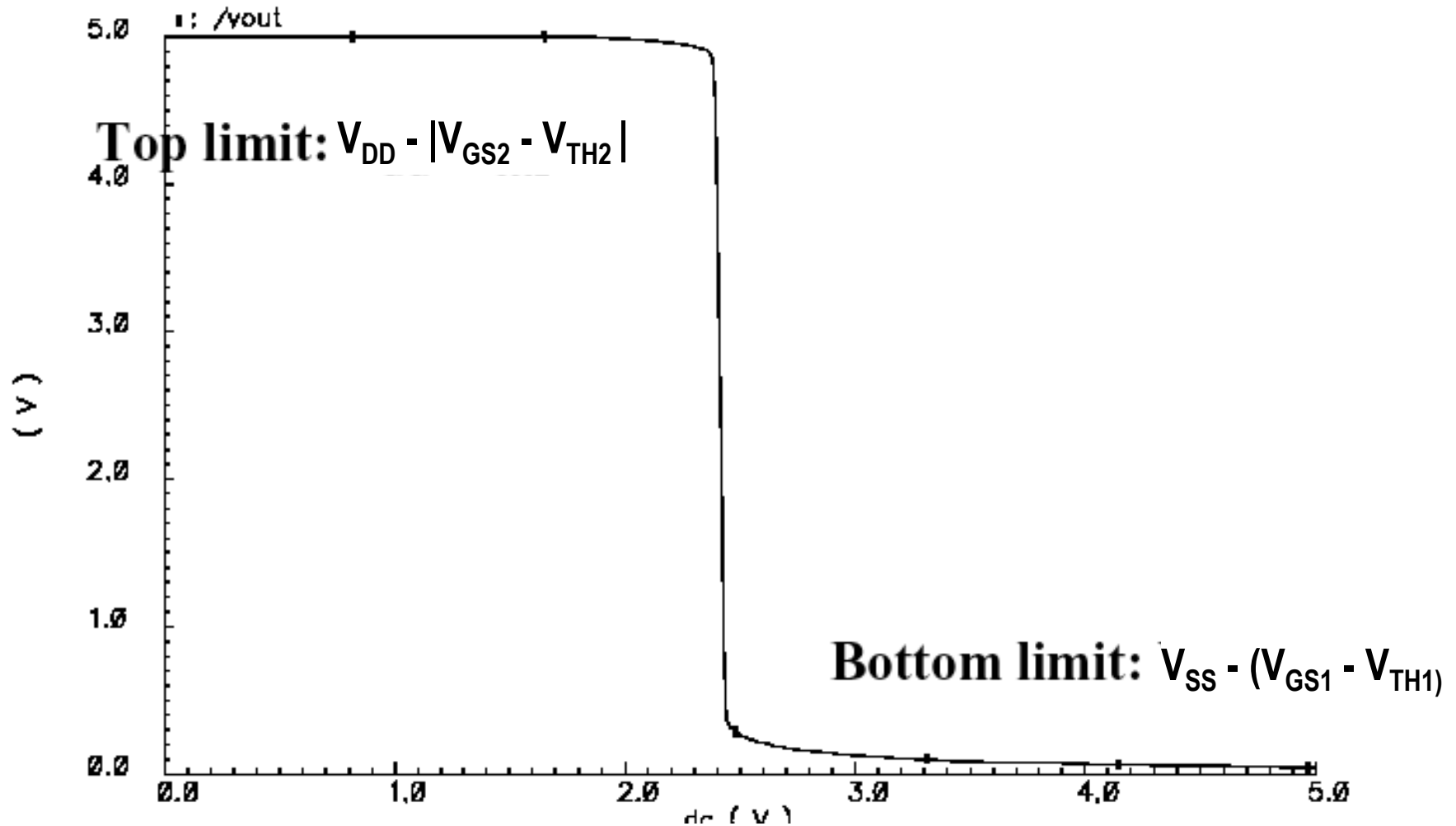
- DC Sweep Schematic



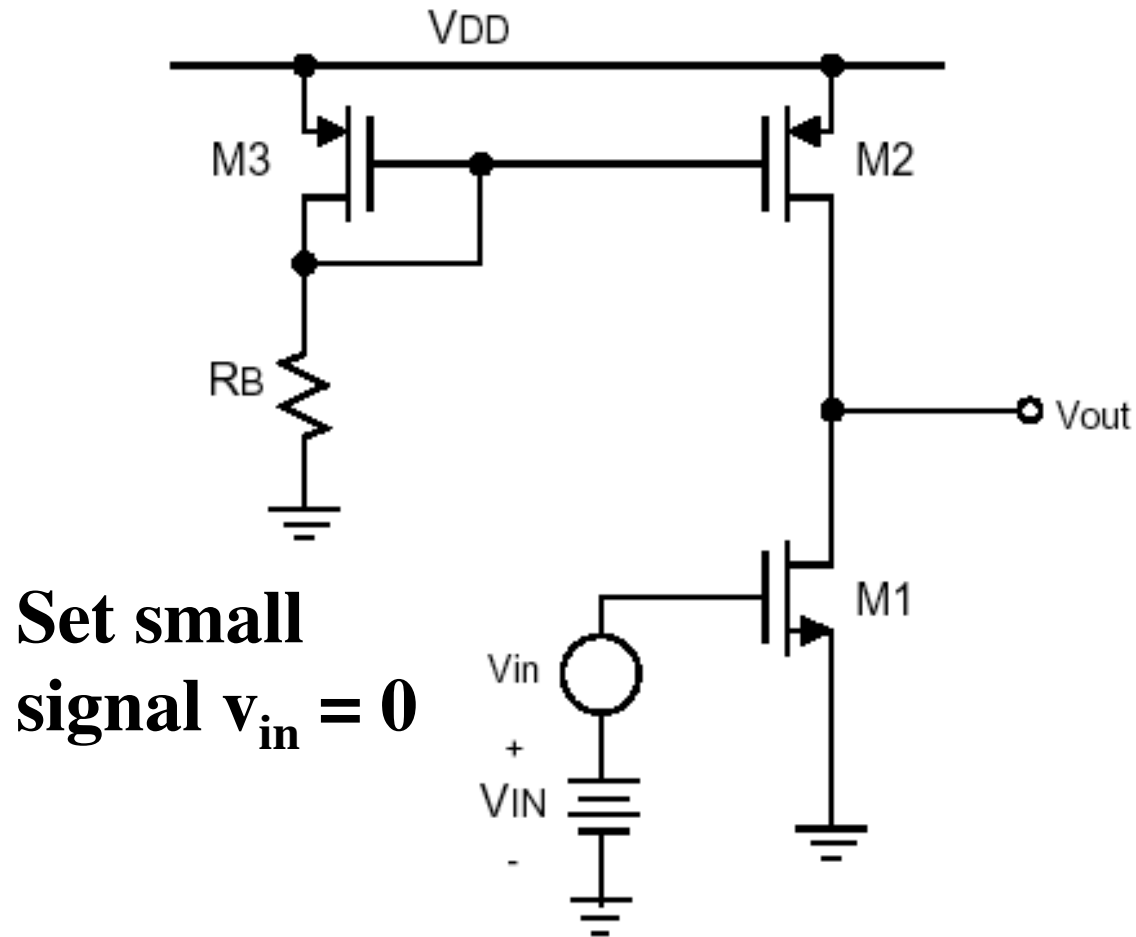
Active Load Simulation Result (DC Sweep)

4902new csactiveload schematic : Jan 26 20:42:10 2002

DC Response

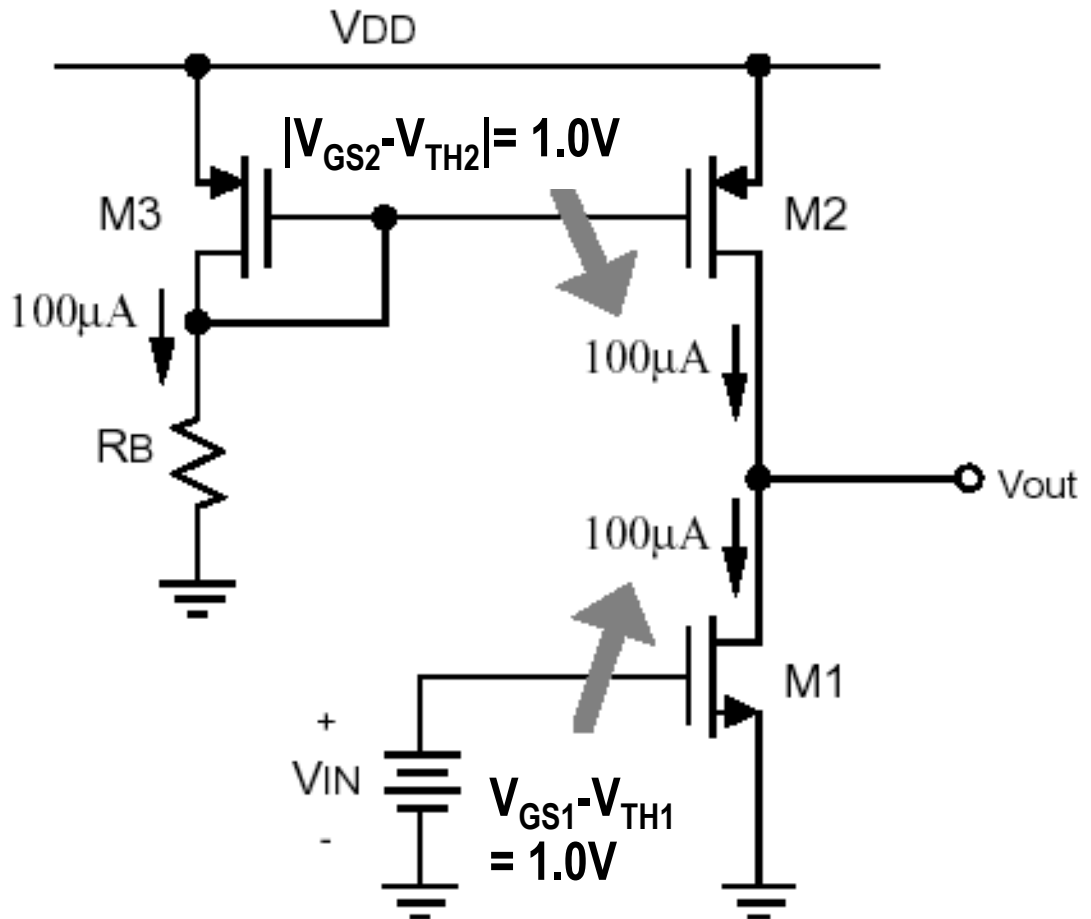


Determining DC Operating Point



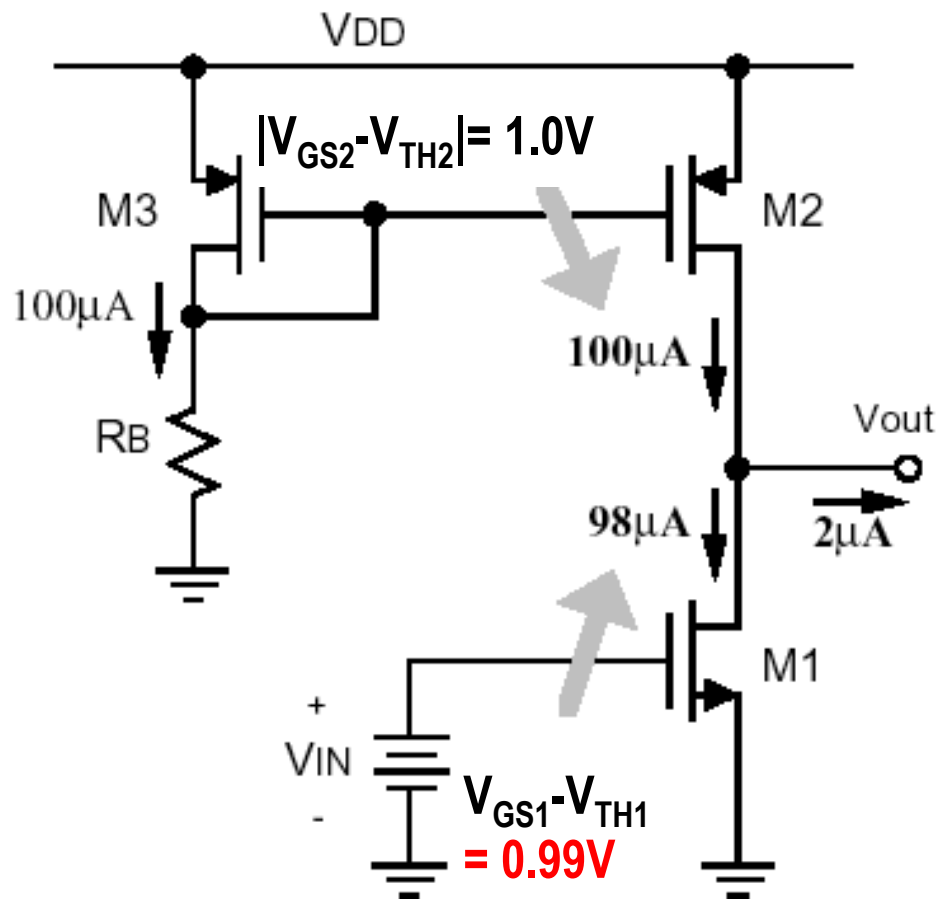
Determining DC Operating Point

- **Active region:**
 $V_{GS} - V_{TH}$
determines I_D
- **Correct V_{IN} :**
M1, M2 “agree”
- **Example:**
 $V_{GS} - V_{TH} = 1.0V$
 $I_D = 100\ \mu A$



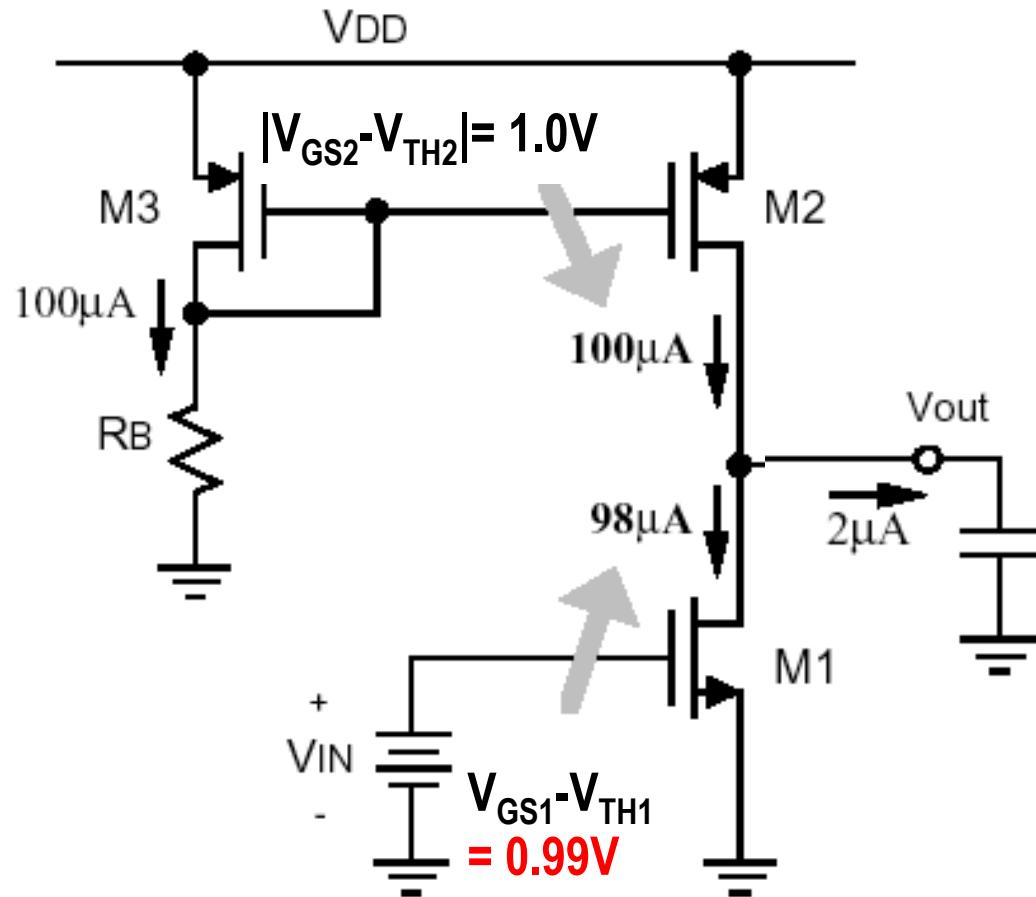
If DC bias at input is “wrong”?

- Current source “disagreement”
- KCL crisis at output: $2\mu\text{A}$, nowhere to go
- What happens?



If DC bias at input is “wrong”?

- Capacitance at output node V_{out}
- $2\mu\text{A}$ flows into cap, charges up:
 - $\Rightarrow V_{DS1}$ increases
 - $\Rightarrow I_1$ increases
 - $\Rightarrow V_{DS2}$ decreases
 - $\Rightarrow I_2$ decreases
- Changes in V_{DS} cause changes in I_D until “agreement” is reached: $I_{D1} = I_{D2}$



How much change in V_{DS} ?

- Changes in V_{DS} cause changes in I_D until “agreement” is reached: $I_{D1} = I_{D2}$ BUT
- Saturation: I_D is a weak function of V_{DS}
- Large change in V_{DS} for small change in I_D
- Output very sensitive to changes in I_D :
- Small ΔV_{GS} at input $\Rightarrow$ Small $\Delta I_D \Rightarrow$
Requires large ΔV_{DS} at output for I_D agreement

Good: high voltage gain

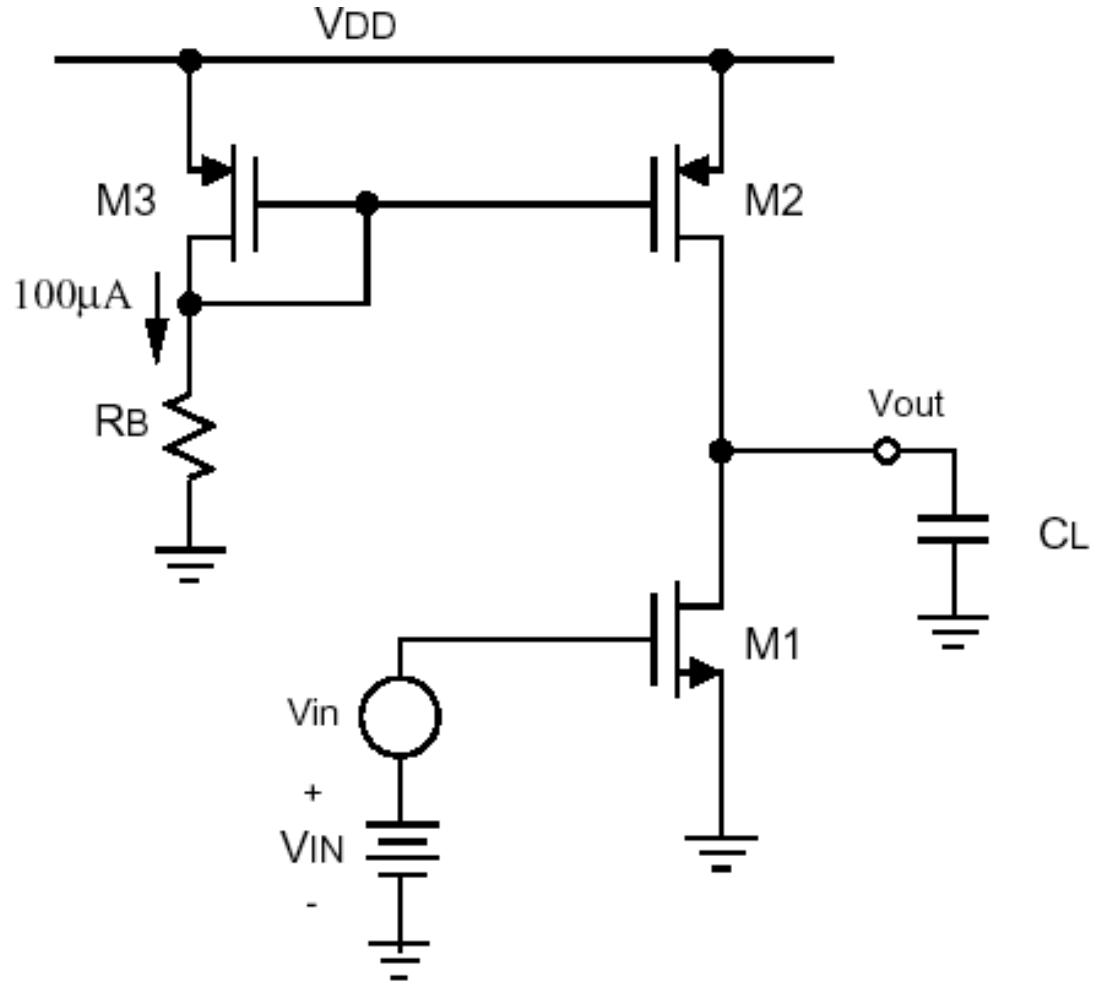
Bad: tricky to get correct input bias point

Frequency Domain Considerations

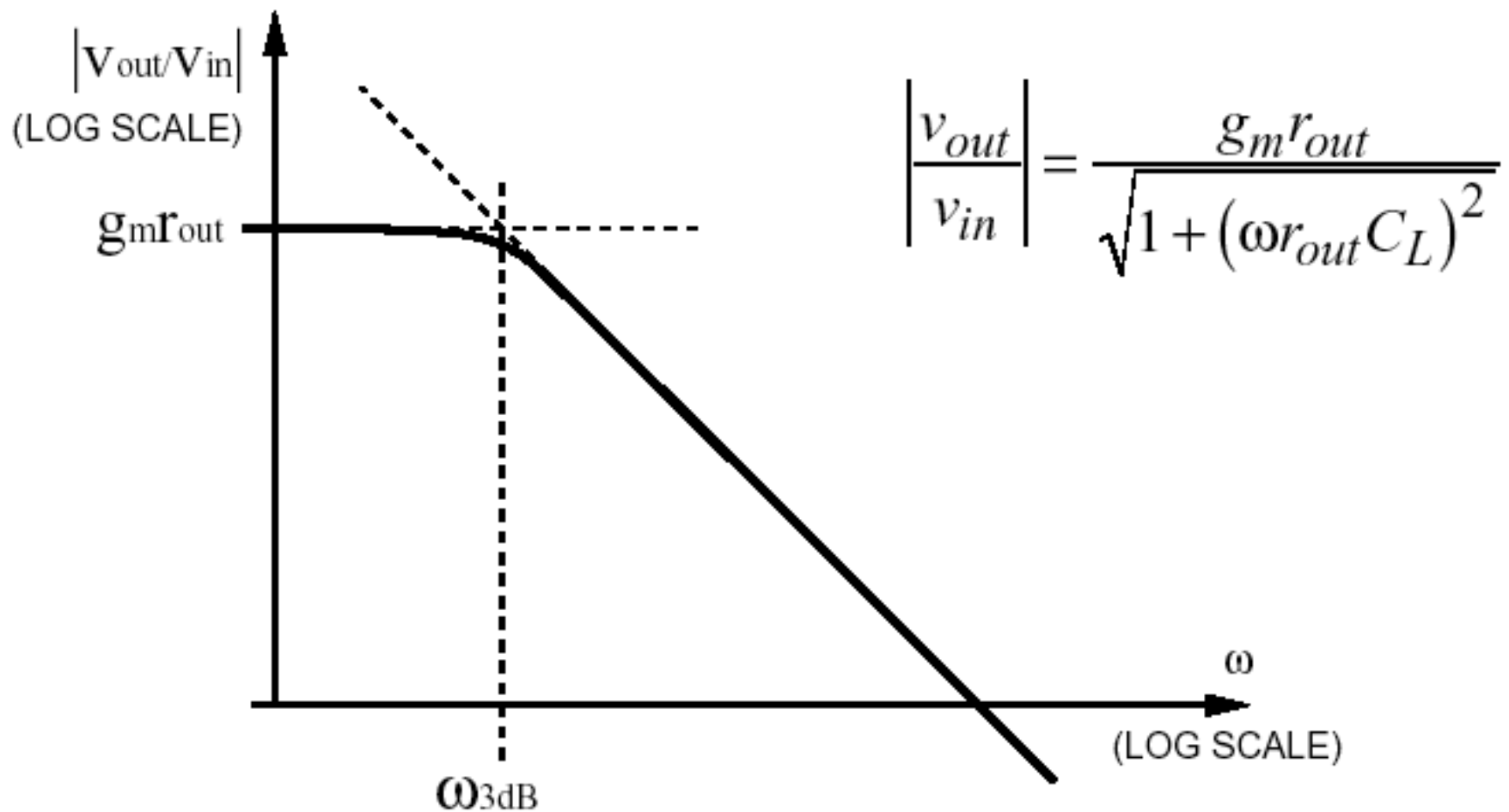
- **Ideal op-amp goals:**
 - **Infinite gain**
 - **Infinite bandwidth**
- **Active load helps gain**
- **What about bandwidth?**

Frequency Domain Analysis

- **Start simple:**
Assume single C_L at output
- (Ignore MOS capacitances for now ...)
- Find transfer function v_{out}/v_{in}



Bode Plot of Transfer Function Magnitude



Bandwidth: ω_{3dB}